

8.2.3 理想p-n结的J-V关系

$$-$$
小注入 $\Delta n_p << p_{p0}$ $\Delta p_n << n_{n0}$ $-$ 突变耗尽层条件 (耗尽层外电中性)

一非简并 扩散电流组成 **电流密度**
$$J = J_p(x_n) + J_n(x_n)$$

$$J = J_p + J_n \qquad = J_p(x_n) + J_n(-x_p)$$

$$= J_p + J_n \qquad = J_p(x_n) + J_n(-x_p)$$

$$= (x-x) \qquad [a]$$

$$J = J_p + J_n - J_p(x_n) + J_n(-x_p)$$

$$\Delta p(x) = \Delta p(x_n) \exp\left(-\frac{x - x_n}{L_n}\right) + \Delta p(x_n) = p_{n0} \left[\exp\left(\frac{qV}{kT}\right) - 1\right]$$

$$\mathbf{p}_{\mathbf{p}0}$$
 $\mathbf{p}_{\mathbf{p}0}$ $\mathbf{p}_{\mathbf{p}0}$ $\mathbf{p}_{\mathbf{p}0}$ $\mathbf{p}_{\mathbf{p}0}$

$$J = J_p + J_n$$

$$J_p$$

$$J_n$$

$$J_p$$

$$\begin{array}{c|c} \mathbf{J_n} & \mathbf{J_p} \\ \hline \mathbf{J_n} & \mathbf{X_n} & \mathbf{X} \\ \hline \mathbf{X}_p) = \frac{qD_n}{L} n_{p0} \left[\exp\left(\frac{qV}{kT}\right) - 1 \right] \end{array}$$

$$J_{p}(x_{n}) = -qD_{p}\frac{d\Delta p}{dx}\Big|_{x=x_{n}} = \frac{qD_{p}}{L_{p}}p_{n0}\left[\exp\left(\frac{qV}{kT}\right) - 1\right] + J_{n}(-x_{p}) = \frac{qD_{n}}{L_{n}}n_{p0}\left[\exp\left(\frac{qV}{kT}\right) - 1\right]$$

$$J_{s} = \left(\frac{qD_{p}n_{i}^{2}}{L_{n}N_{D}} + \frac{qD_{n}n_{i}^{2}}{L_{n}N_{A}}\right) \quad p_{n0} = \frac{n_{i}^{2}}{N_{D}} \quad n_{p0} = \frac{n_{i}^{2}}{N_{A}} \rightarrow J_{s}\left[\exp\left(\frac{qV}{kT}\right) - 1\right]$$

8.2.4 理想p-n结J-V关系的特性

$$J = J_s \left[\exp\left(\frac{qV}{kT}\right) - 1 \right] J_s = \left(\frac{qD_p n_i^2}{L_p N_D} + \frac{qD_n n_i^2}{L_n N_A}\right)$$



一强烈依赖温度

$$J_s \propto T^{3+\frac{\gamma}{2}} \exp(-\frac{E_g}{kT})$$

$$J \propto T^{3+\frac{\gamma}{2}} \exp\left[\frac{q(V-V_{g0})}{kT}\right]$$

8.2.5 理想p-n结J-V关系的修正

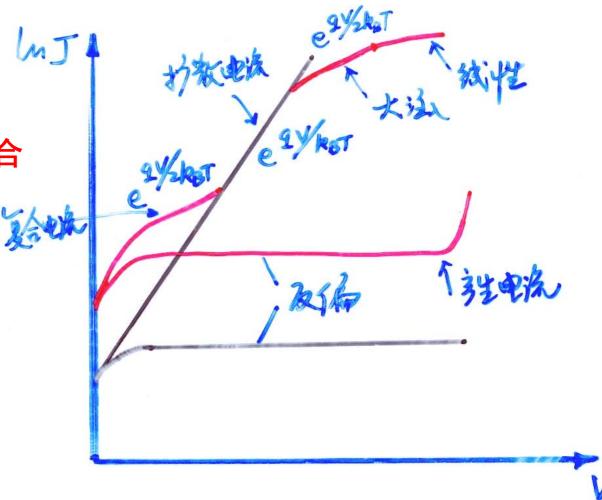
可能因素:

一表面效应

一势垒区中的产生和复合

一大注入条件

一串联电阻



8.2.5 理想p-n结J-V关系的修正

假设
$$E_t = E_i$$
, $n_1 = p_1 = n_i$, $r_n = r_p = r$

$$U = \frac{N_t r_n r_p (np - n_i^2)}{r_n (n + n_1) + r_p (p + p_1)} = \frac{N_t r (np - n_i^2)}{n + p + 2n_i}$$

$$n = n_i \exp\left(\frac{E_F^n - E_i}{kT}\right)$$

$$p = n_i \exp\left(\frac{E_i - E_F^p}{kT}\right)$$

$$n = n_i \exp\left(\frac{E_F - E_i}{kT}\right)$$

$$p = n_i \exp\left(\frac{E_i - E_F^p}{kT}\right)$$

$$np = n_i^2 \exp\left(\frac{E_F - E_F^p}{kT}\right) = n_i^2 \exp\left(qV_f/kT\right)$$

$$U_{\text{max}} = \frac{1}{2} \frac{n_i}{\tau} \exp(qV_f / 2kT) \qquad (qV_f >> kT)$$

8.2.5 理想p-n结J-V关系的修正

$$\begin{array}{c|c} - \underline{\mathfrak{D}} \triangleq \mathbb{R}(\mathbb{E} \, | \, \mathbf{h} \, \mathbf{E}) \\ \hline & U_{\max} = \frac{1}{2} \frac{n_i}{\tau} \exp \left(q V_f / 2kT\right) & \left(q V_f >> kT\right) \\ \hline & D_{\max} = \int_{-x_p}^{x_n} q U_{\max} dx = q U_{\max} X_D = \frac{q n_i X_D}{2\tau} \exp \left(q V_f / 2kT\right) \\ \hline & \mathbf{p} & \mathbf{n} \\ \hline & \mathbf{p} & \mathbf{p}$$

理想因子 m:1~2

8.2.5 理想p-n结J-V关系的修正

一产生电流(反向偏压)

$$n_{i} >> n, p; E_{t} = E_{i}; r_{n} = r_{p} = r$$

$$\downarrow$$

$$U = \frac{N_{t}r_{n}r_{p}(np - n_{i}^{2})}{r_{n}(n + n_{1}) + r_{p}(p + p_{1})} = -\frac{n_{i}}{2\tau}$$

- 一J_s与反向偏压无关,J_G随反向偏压增加而增加
- 一禁带宽度小的半导体,反向漏电流将 明显增加
- 一温度升高,反向漏电流将增加
- 一少子寿命越小,反向漏电流也就越大

$$J_{G} = qGX_{D} = q\frac{n_{i}}{2\tau}X_{D}$$

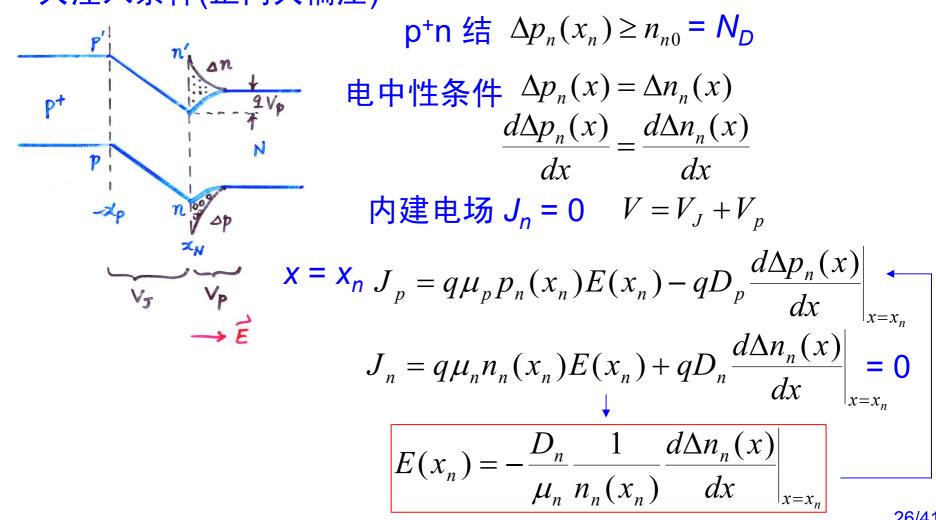
$$G = -U = \frac{n_{i}}{2\tau}$$

$$\frac{J_{rd}}{J_{G}} = 2\frac{n_{i}}{N_{D}}\frac{L_{p}}{X_{D}}$$

$$J_{rd} = J_{s} = \frac{qD_{p}n_{i}^{2}}{L_{p}N_{D}}$$

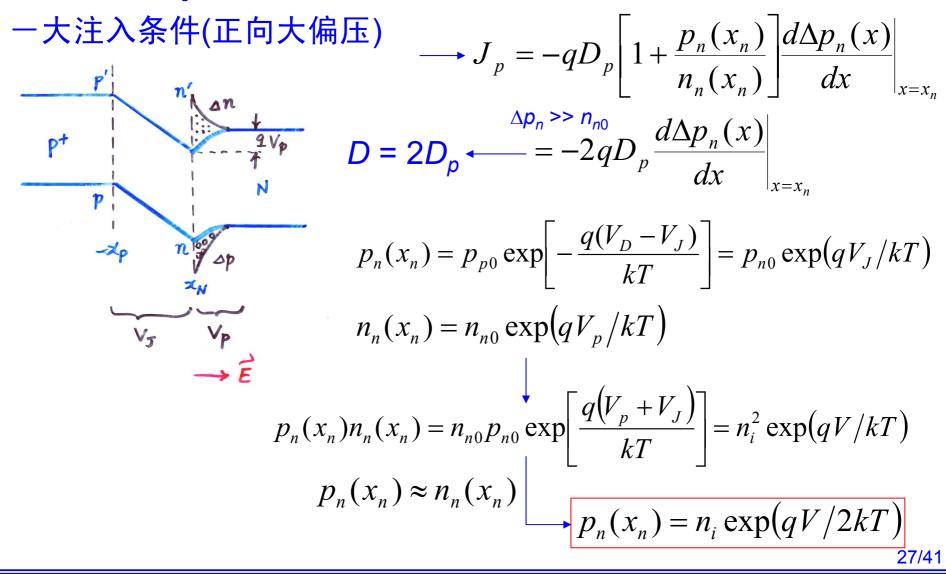
8.2.5 理想p-n结J-V关系的修正

一大注入条件(正向大偏压)



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8.2.5 理想p-n结J-V关系的修正



8.2.5 理想p-n结J-V关系的修正

一大注入条件(正向大偏压)

$$p_n(x_n) = n_i \exp(qV/2kT)$$
 $\rightarrow J_p = -2qD_p \frac{d\Delta p_n(x)}{dx} \Big|_{x=x_n}$ 线性分布近似 $\frac{d\Delta p_n(x)}{dx} \Big|_{x=x_n}$ $\approx -\frac{p_n(x_n) - p_{n0}}{L_p} \approx -\frac{n_i}{L_p} \exp(qV/2kT)$

8.2.5 理想p-n结J-V关系的修正

